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L19: (23) 18 not 16

L20: (9) (US-4951100-S or US-5619450-S or US-5040

L21: (22) 19 not 20

Failed

(0) 8 and (p-type or (

(0) (T-RAM and (defusis adj2 region))

(0) (T-RAM.ti.

(0) 13 and (dop\$3 near2 (portion or region)

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(1516) TRAM or T-RAM

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((TRAM or T-RAM) and thyristor) not (((TRAM or T-RAM) and thyristor) and

((transfer adj gate) or (pass\$4 adj gate)))

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	U	I	PT	P	Document ID	Issue Dat	Pages	Title	Current OR	Current XR	Retrieval	Inventor	S	C	2	3	4
1					US	20020815	26	Semiconductor device	257/107			Kajiyama, Takeshi					
					20020109150			and manufacturing metho									
2					US	20020725	16	Manufacture of	257/133	257/E29.33		Nemati, Farid et					
					20020096690			semiconductor capacitiv		7		al.					
3					US	20020725	15	Semiconductor	257/107	257/E29.33		Nemati, Farid et					
					20020096689			capacitively-coupled ND		7		al.					
4					US	20020711	64	Magnetoresistive memory	257/421			Iwata, Yoshihisa					
					20020089024			device									
5					US	6479862	18	Charge trapping device	257/321	257/295;		King, Tou-Jae et					
					B1			and method for implemen		257/317;		al.					
6					US	6462359	15	Stability in	257/107	257/109;		Nemati, Farid et					
					B1			thyristor-based memory		257/137;		al.					
7					US	6448586	16	Semiconductor	257/133	257/147;		Nemati, Farid et					
					B1			current-switching devic		257/155;		al.					
8					US	6250442	22	Ground power supply for	191/6	191/18;		Perraud, Olivier					
					B1			electric vehicle with e		191/14;		et al.					
9					US	6157148	13	Contactless	318/49	318/139;		Posma, Bonne W.					
					A			multi-motor controller		318/293;							
10					US	5070697	11	Actuator with memory	60/527	188/282.4;		Van Zeggeren,					
					A			metal and a shock absor		188/213		Wilhelm A.					
11					US	4070605	17	Polyphase power control	318/758	318/741;		Hoepfner, Conrad					
					A					318/809;		H.					
12					US	3577055	4	MEANS FOR REPRESENTATIVE	318/376	318/370;		Watanabe					

Ready

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L Number	Hits	Search Text	DB	Time stamp
11	75	joshi-rajiv-v.in.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/04 16:50
12	52	assaderaghi-fariborz.in.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/04 16:50
13	13	moy-dan.in.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/04 16:50
14	45	rausch-werner.in.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/04 16:50
15	1	culp-james.in.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/04 16:51
16	173	joshi-rajiv-v.in. assaderaghi-fariborz.in. moy-dan.in. rausch-werner.in. culp-james.in.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/04 16:51
17	7	(joshi-rajiv-v.in. assaderaghi-fariborz.in. moy-dan.in. rausch-werner.in. culp-james.in.) and ("TRAM" or ("T-RAM"))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/04 16:55
18	30	((("TRAM" or ("T-RAM"))) adj cell)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/04 16:56
19	23	((("TRAM" or ("T-RAM"))) adj cell)) not (joshi-rajiv-v.in. assaderaghi-fariborz.in. moy-dan.in. rausch-werner.in. culp-james.in.)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/04 16:56
20	9	(US-4951100-\$ or US-5619450-\$ or US-5040043-\$ or US-5177405-\$ or US-3918033-\$ or US-6229161-\$ or US-5981984-\$).did. or (US-20020093030-\$ or US-20020100918-\$).did.	USPAT; US-PGPUB	2003/09/04 16:58
21	22	((("TRAM" or ("T-RAM"))) adj cell)) not (joshi-rajiv-v.in. assaderaghi-fariborz.in. moy-dan.in. rausch-werner.in. culp-james.in.) not ((US-4951100-\$ or US-5619450-\$ or US-5040043-\$ or US-5177405-\$ or US-3918033-\$ or US-6229161-\$ or US-5981984-\$).did. or (US-20020093030-\$ or US-20020100918-\$).did.)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/04 16:58
-	1516	TRAM or T-RAM	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/24 20:43
-	19	(TRAM or T-RAM) and thyristor	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/24 20:43
-	3	((TRAM or T-RAM) and thyristor) and ((transfer adj gate) or (pass\$4 adj gate))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/24 21:33
-	16	((TRAM or T-RAM) and thyristor) not (((TRAM or T-RAM) and thyristor) and ((transfer adj gate) or (pass\$4 adj gate)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/24 21:43
-	5	"6229161"	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/24 21:34

-	1497	((TRAM or T-RAM) not ((TRAM or T-RAM) and thyristor))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/24 21:43
-	197	((TRAM or T-RAM) not ((TRAM or T-RAM) and thyristor)) and gate	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/24 21:43
-	100	((((TRAM or T-RAM) not ((TRAM or T-RAM) and thyristor)) and gate) and transistor	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/24 21:44
-	0	(((((TRAM or T-RAM) not ((TRAM or T-RAM) and thyristor)) and gate) and transistor) and halo	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/24 21:45
-	0	(((((TRAM or T-RAM) not ((TRAM or T-RAM) and thyristor)) and gate) and transistor) and ((punch adj through) or (punch-through))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/24 21:46
-	0	(((((TRAM or T-RAM) not ((TRAM or T-RAM) and thyristor)) and gate) and ((punch adj through) or (punch-through))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/24 21:47
-	3	(((((TRAM or T-RAM) not ((TRAM or T-RAM) and thyristor)) and gate) and transistor) and (p-type or ("p" adj type))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/24 21:50
-	84	(((((TRAM or T-RAM) not ((TRAM or T-RAM) and thyristor)) and gate) and transistor) and memory	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/24 21:50
-	84	(((((TRAM or T-RAM) not ((TRAM or T-RAM) and thyristor)) and gate) and transistor) and memory) and transistor	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/24 21:50
-	32293	thyristor	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/24 21:53
-	761	thyristor and (RAM or MEM)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/24 21:53
-	2729	thyristor and (RAM or MEM or memory)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/24 21:53
-	1603	((thyristor and (RAM or MEM or memory)) and transistor	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/24 21:53
-	45	((thyristor and (RAM or MEM or memory)) and transistor) and (gate near2 transfer)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/24 21:54
-	118	((thyristor and (RAM or MEM or memory)) and transistor) and (gate near2 pass\$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/24 21:54
-	152	((((thyristor and (RAM or MEM or memory)) and transistor) and (gate near2 transfer)) or (((thyristor and (RAM or MEM or memory)) and transistor) and (gate near2 pass\$4)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/24 21:55
-	143	(((((thyristor and (RAM or MEM or memory)) and transistor) and (gate near2 transfer)) or (((thyristor and (RAM or MEM or memory)) and transistor) and (gate near2 pass\$4))) and device	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/24 21:59

-	3	(((thyristor and (RAM or MEM or memory)) and transistor) and (gate near2 transfer)) or (((thyristor and (RAM or MEM or memory)) and transistor) and (gate near2 pass\$4))) and device) and (p-mos or ("P" adj "MOS"))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/24 22:01
-	0	20020158254.URPN.	USPAT	2002/11/24 22:00
-	0	20020151130.URPN.	USPAT	2002/11/24 22:01
-	243	Hsu-louis-\$.in.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/24 22:02
-	0	Hsu-louis-\$.in. and ("TMOS" or "T-MOS")	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/24 22:03
-	0	Hsu-louis-\$.in. and (TMOS or T-MOS)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/24 22:03
-	5	Hsu-louis-\$.in. and ("TRAM" or "T-RAM")	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/24 22:04
-	2	(T-RAM or TRAM) near2 array.ti.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/24 22:40
-	2	((("6104045") or ("5824584"))).PN.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 11:16
-	15	("4543595" "4720845" "5173754" "5214295" "5286663" "5486717" "5497011" "5535156" "5581104" "5594683" "5624863" "5650350" "5684737" "5705843" "5710741").PN.	USPAT	2002/11/25 09:39
-	8	("4837173" "4951100" "5013675" "5063172" "5408115" "5422504" "5467308" "5470794").PN.	USPAT	2002/11/25 11:10
-	2381	T-RAM or "P-N-P-N" or "PNPN"	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 11:19
-	547	(T-RAM or "P-N-P-N" or "PNPN") and polarity	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 11:19
-	417	((T-RAM or "P-N-P-N" or "PNPN") and polarity) and transistor	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 11:20
-	40	(((T-RAM or "P-N-P-N" or "PNPN") and polarity) and transistor) and ((transfer\$3 near gate) or (transfer) or (passing adj gate))) and (p-type or (p-body))) and (device)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 11:46
-	23	("4094012" "4289982" "4443718" "4446536" "4649521" "4694430" "4742492" "4761764" "4774421" "4804637" "4820941" "4823318" "4862019" "4893275" "4939558" "4956816" "4975883" "5008856" "5010520" "5157280" "5175704" "5265052" "5336952").PN.	USPAT	2002/11/25 11:28
-	4	("4079506" "4593458" "4685198" "4767722").PN.	USPAT	2002/11/25 11:43

-	15	T-RAM and ((transfer) or (pass\$4))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 11:47
-	0	20020093030.URPN.	USPAT	2002/11/25 11:53
-	0	20020093030.URPN.	USPAT	2002/11/25 11:53
-	24	("3918033" "3986177" "4090254" "4146902" "4590589" "4612448" "4677455" "5321285" "5324966" "5390145" "5396454" "5412598" "5464994" "5471419" "5525820" "5543652" "5587944" "5689458" "5874751" "5910738" "5914503" "5936267" "5939736" "5981984").PN.	USPAT	2002/11/25 11:54
-	1	"3697962".PN.	USPAT	2002/11/25 11:57
-	8	3918033.URPN.	USPAT	2002/11/25 11:58
-	0	6448586.URPN.	USPAT	2002/11/25 11:58
-	85	((T-RAM or "P-N-P-N" or "PNPN") and polarity) and transistor) and ((transfer\$3 near gate) or (transfer) or (passing adj gate))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 15:21
-	44	((T-RAM or "P-N-P-N" or "PNPN") and polarity) and transistor) and ((transfer\$3 near gate) or (transfer) or (passing adj gate))) and (p-type or (p-body))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 15:21
-	41	((T-RAM or "P-N-P-N" or "PNPN") and polarity) and transistor) and ((transfer\$3 near gate) or (transfer) or (passing adj gate))) not (((T-RAM or "P-N-P-N" or "PNPN") and polarity) and transistor) and ((transfer\$3 near gate) or (transfer) or (passing adj gate))) and (p-type or (p-body)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 15:43
-	41	((T-RAM or "P-N-P-N" or "PNPN") and polarity) and transistor) and ((transfer\$3 near gate) or (transfer) or (passing adj gate))) not (((T-RAM or "P-N-P-N" or "PNPN") and polarity) and transistor) and ((transfer\$3 near gate) or (transfer) or (passing adj gate))) and (p-type or (p-body))) and polarity	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 15:47
-	0	(T-RAM and (defusi\$3 adj2 region))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 15:48
-	0	(T-RAM and (deffusi\$3 adj2 region))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 15:49
-	0	(T-RAM and (impurity\$3 adj2 region))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 15:49
-	6	(T-RAM and (channel adj2 region))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 15:51
-	0	20020093030.URPN.	USPAT	2002/11/25 15:50
-	3	T-RAM.ti.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 15:53

-	803	("NDR" or (negative adj different\$4 adj resistanc\$4))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 16:26
-	78	((("NDR" or (negative adj different\$4 adj resistanc\$4))) and "SRAM")	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 15:56
-	50	((("NDR" or (negative adj different\$4 adj resistanc\$4))) and "SRAM") and "DRAM"	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 15:56
-	48	((("NDR" or (negative adj different\$4 adj resistanc\$4))) and "SRAM") and "DRAM") and transistor	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 15:56
-	10	((("NDR" or (negative adj different\$4 adj resistanc\$4))) and "SRAM") and "DRAM") and transistor) and "T-RAM"	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 16:01
-	27	((("NDR" or (negative adj different\$4 adj resistanc\$4))) and "SRAM") and "DRAM") and (dop\$3 near2 (portion or region))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 16:04
-	4	((("NDR" or (negative adj different\$4 adj resistanc\$4))) and "SRAM") and "DRAM") and (deplet\$5 near2 region)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 16:10
-	15	("4543595" "4720845" "5173754" "5214295" "5286663" "5486717" "5497011" "5535156" "5581104" "5594683" "5624863" "5650350" "5684737" "5705843" "5710741").PN.	USPAT	2002/11/25 16:07
-	22	((("NDR" or (negative adj different\$4 adj resistanc\$4))) and "SRAM") and "DRAM") and (dop\$3 near2 (portion or region)) not (((("NDR" or (negative adj different\$4 adj resistanc\$4))) and "SRAM") and "DRAM") and (deplet\$5 near2 region)) or ("4543595" "4720845" "5173754" "5214295" "5286663" "5486717" "5497011" "5535156" "5581104" "5594683" "5624863" "5650350" "5684737" "5705843" "5710741").PN.)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 16:24
-	17	T-RAM or "T-RAM"	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 16:25
-	776	((("NDR" or (negative adj different\$4 adj resistanc\$4))) not (((("NDR" or (negative adj different\$4 adj resistanc\$4))) and "SRAM") and "DRAM") and (dop\$3 near2 (portion or region)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 16:26
-	316	((("NDR" or (negative adj different\$4 adj resistanc\$4))) not (((("NDR" or (negative adj different\$4 adj resistanc\$4))) and "SRAM") and "DRAM") and (dop\$3 near2 (portion or region)))) and (dop\$4 or deplet\$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 16:35
-	14	"5619450"	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 17:12
-	243	hsu-louis-\$.in.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 17:12
-	4	hsu-louis-\$.in. and (T-RAM)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 17:13

-	4	hsu-louis-\$.in. and ("NDR" or (negative adj different\$4 adj resist\$4))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/25 17:17
-	0	("T-RAM" or "TRAM") and (horizontal adj device)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/04/24 15:31
-	486	("T-RAM" or "TRAM") and (horizontal)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/04/24 15:31
-	8	((("T-RAM" or "TRAM") and (horizontal)) and (thyristor))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/04/24 15:42
-	1	"6552398"	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/04/24 16:47
-	10	("3831187" "3943549" "4112505" "4165517" "4281336" "4323793" "4646121" "4982258" "5463344" "6229161").PN.	USPAT	2003/04/24 15:50
-	12	"5324966"	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/04/24 16:57
-	21	"4502070"	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/04/24 16:57